Photocouplers Infrared LED & Photo Triac

TLP3052A,TLP3052AF

1. Applications

- Solid-State Relays
- Triac Drivers
- Home Electric Appliances
- Office Equipment

2. General

The TLP3052A consists of a non zero crossing photo triac, optically coupled to an infrared LED. The TLP3052A is housed in the DIP6 package and guarantees insulation thickness of 0.4 mm (min). Therefore, the TLP3052A meets the reinforced insulation class requirements of international safety standards.

3. Features

(1) Halogen-free
For details, see "Devices in Halogen-Free Resin Packages" at the end of this datasheet.
(2) Peak off-state voltage: 600 V (min)
(3) Non zero crossing functionary (NZC)
(4) Trigger LED current: 10 mA (max)
(5) On-state current: 100 mA (max)
(6) Isolation voltage: 5000 Vrms (min)
(7) Safety standards
UL-recognized: UL 1577, File No.E67349
cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349
VDE-approved: EN IEC 60747-5-5, EN IEC 62368-1 **(Note 1)**
CQC-approved: GB4943.1 Japan Factory

Note 1: When a VDE approved type is needed, please designate the **Option (D4)**.

Table 3.1 Mechanical Parameters

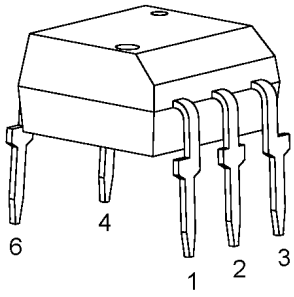
Characteristics	7.62 mm Pitch TLP3052A	10.16 mm Pitch TLP3052AF	Unit
Creepage distances	7.0 (min)	8.0 (min)	mm
Clearance distances	7.0 (min)	8.0 (min)	
Internal isolation thickness	0.4 (min)	0.4 (min)	

Start of commercial production
2015-08

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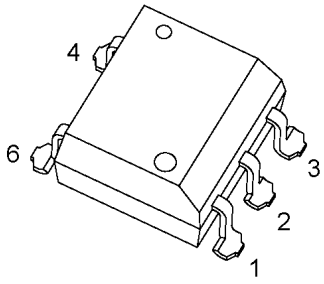
4. Packaging (Note)

TLP3052A



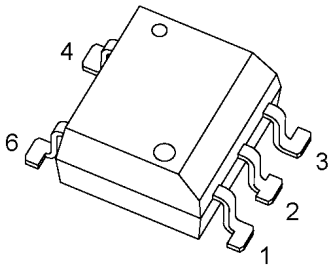
11-7A10S

TLP3052A(LF1,TP1)



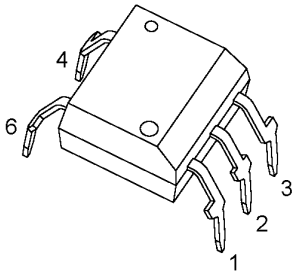
11-7A1001S

TLP3052A(LF5,TP5)



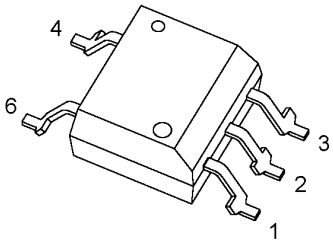
11-7A1005S

TLP3052AF



11-7A1002S

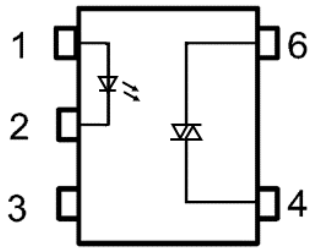
TLP3052AF(LF4,TP4)



11-7A1004S

Note: Through-hole type: TLP3052A, TLP3052AF
Lead forming option: (LF1), (LF4), (LF5)
Taping option: (TP1), (TP4), (TP5)

5. Pin Assignment



1: Anode
2: Cathode
3: N.C.
4: Triac terminal
6: Triac terminal

6. Product Naming Conventions

Type of package used for shipment is denoted by a symbol suffix after a part number. The method of classification is as below.

Example) TLP3052A(TP1,F

Part number: TLP3052A
Tape type: TP1 **(Note 1)**
[[G]]/RoHS COMPATIBLE: F **(Note 2)**

Note 1: At the part of tape type, below options are used including lead forming type.
TLP3052A: LF1, TP1, LF5, TP5
TLP3052AF: LF4, TP4

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.
RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

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7. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C)

	Characteristics		Symbol	Note	Rating	Unit
LED	Input forward current		I_F		50	mA
	Input forward current derating	($T_a \geq$ 53 °C)	$\Delta I_F/\Delta T_a$		-0.7	mA/°C
	Input forward current (pulsed)		I_{FP}	(Note 1)	1	A
	Input reverse voltage		V_R		5	V
	Input power dissipation		P_D		100	mW
	Input power dissipation derating	($T_a \geq$ 25 °C)	$\Delta P_D/\Delta T_a$		-1.0	mW/°C
	Junction temperature		T_j		125	°C
Detector	Off-state output terminal voltage		V_{DRM}		600	V
	R.M.S. on-state current	(T_a = 25 °C)	$I_{T(RMS)}$		100	mA
		(T_a = 70 °C)			50	mA
	R.M.S. on-state current derating	($T_a \geq$ 25 °C)	$\Delta I_{T(RMS)}/\Delta T_a$		-1.1	mA/°C
	ON-state current (pulsed)		I_{ONP}	(Note 2)	2	A
	Peak non-repetitive surge current		I_{TSM}	(Note 3)	1.2	A
	Output power dissipation		P_O		300	mW
	Output power dissipation derating	($T_a \geq$ 25 °C)	$\Delta P_O/\Delta T_a$		-4.0	mW/°C
	Junction temperature		T_j		125	°C
Common	Total power dissipation		P_T		400	mW
	Total power dissipation derating	($T_a \geq$ 25 °C)	$\Delta P_T/\Delta T_a$		-4.4	mW/°C
	Operating temperature		T_{opr}		-40 to 100	°C
	Storage temperature		T_{stg}		-55 to 125	
	Lead soldering temperature	(10 s)	T_{sol}		260	
	Isolation voltage	AC, 60 s, R.H. ≤ 60 %	BV_S	(Note 4)	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width (PW) ≤ 100 μs, 100 pps

Note 2: Pulse width (PW) ≤ 100 μs, 120 pps

Note 3: Pulse width (PW) ≤ 10 ms

Note 4: This device is considered as a two-terminal device: Pins 1, 2 and 3 are shorted together, and pins 4 and 6 are shorted together.

8. Recommended Operating Conditions (Note)

Characteristics	Symbol	Note	Min	Typ.	Max	Unit
AC mains voltage	V_{AC}	(Note 1)	—	—	240	V
Input forward current	I_F		15	20	25	mA
ON-state current (pulsed)	I_{ONP}		—	—	1	A
Operating temperature	T_{opr}		-25	—	85	°C

Note: The recommended operating conditions are given as a design guide necessary to obtain the intended performance of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this data sheet should also be considered.

Note 1: AC use only.

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9. Electrical Characteristics (Unless otherwise specified, T_a = 25 °C)

	Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
LED	Input forward voltage	V_F		I_F = 10 mA	1.0	1.15	1.3	V
	Input reverse current	I_R		V_R = 5 V	—	—	10	μA
	Input capacitance	C_t		V = 0 V, f = 1 MHz	—	30	—	pF
Detector	Peak off-state current	I_{DRM}		V_{DRM} = 600 V	—	10	1000	nA
	Peak on-state voltage	V_{TM}		I_{TM} = 100 mA	—	1.7	3.0	V
	Holding current	I_H		—	—	0.6	—	mA
	Critical rate of rise of off-state voltage	dv/dt		V_{in} = 240 V, T_a = 25 °C See Fig. 9.1	—	2000	—	V/μs
	Critical rate of rise of commutating voltage (dv/dt)	dv/dt(c)		V_{in} = 60 Vrms, I_T = 15 mA See Fig. 9.1	—	0.2	—	

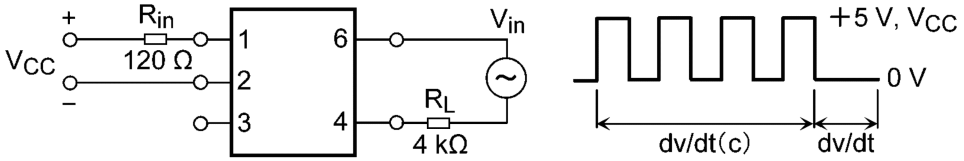


Fig. 9.1 dv/dt Test Circuit and Waveform

10. Coupled Electrical Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Trigger LED current	I_{FT}		V_T = 6 V	—	—	10	mA

11. Isolation Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Total capacitance (input to output)	C_S	(Note 1)	V_S = 0 V, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R_S	(Note 1)	V_S = 500 V, R.H. ≤ 60%	10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S	(Note 1)	AC, 60 s	5000	—	—	Vrms

Note 1: This device is considered as a two-terminal device: Pins 1, 2 and 3 are shorted together, and pins 4 and 6 are shorted together.

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12. Characteristics Curves (Note)

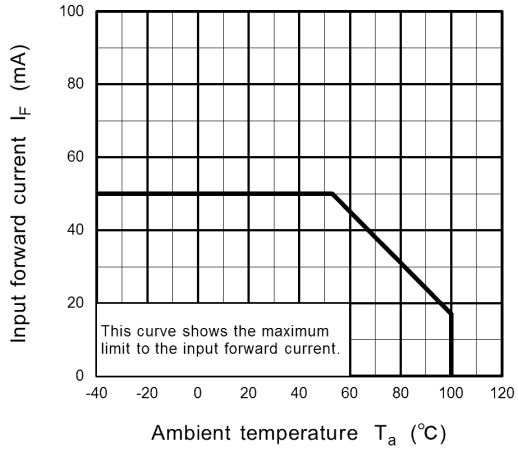


Fig. 12.1 I_F - T_a

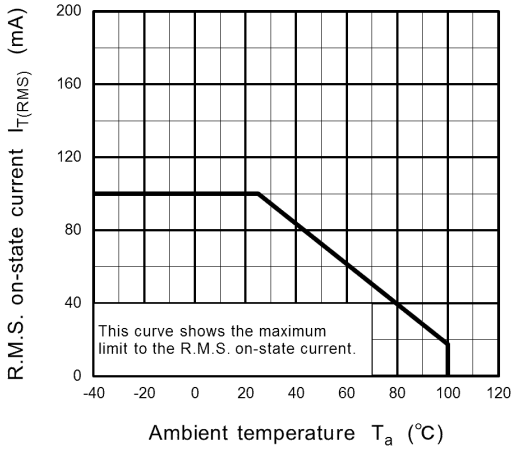


Fig. 12.2 $I_{T(RMS)}$ - T_a

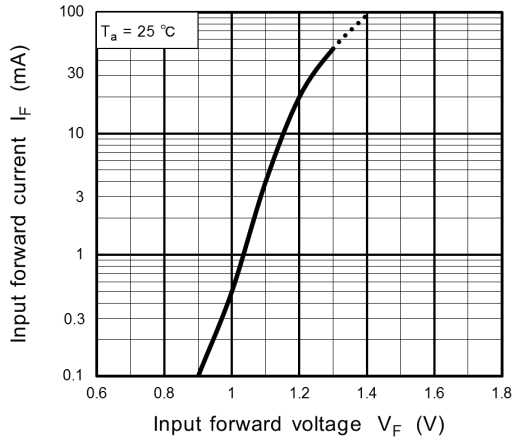


Fig. 12.3 I_F - V_F

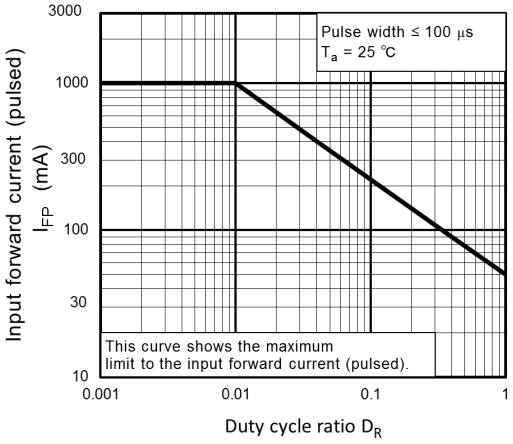


Fig. 12.4 I_{FP} - D_R

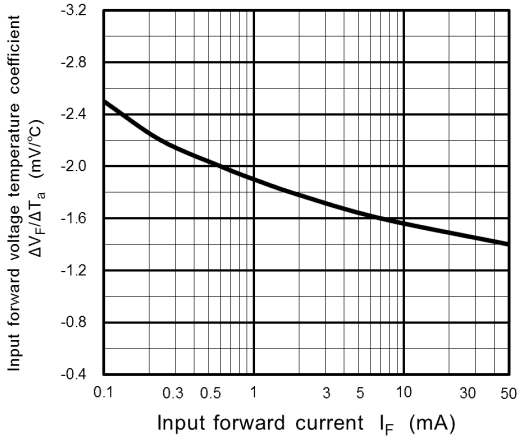


Fig. 12.5 $\Delta V_F/\Delta T_a$ - I_F

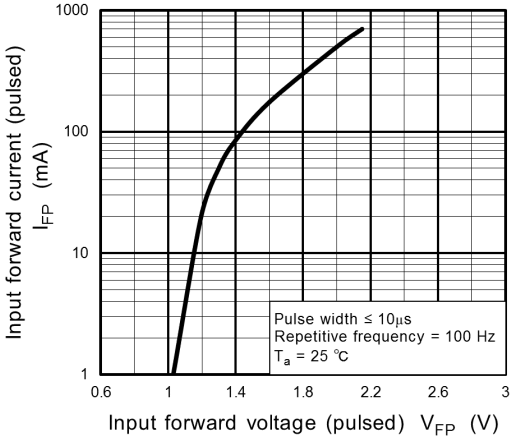


Fig. 12.6 I_{FP} - V_{FP}

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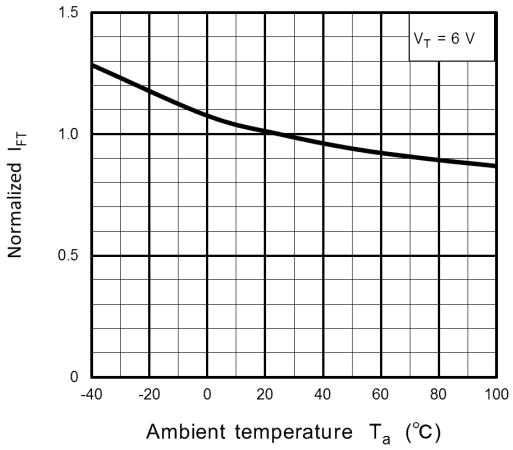


Fig. 12.7 Normalized I_{FT} - T_a

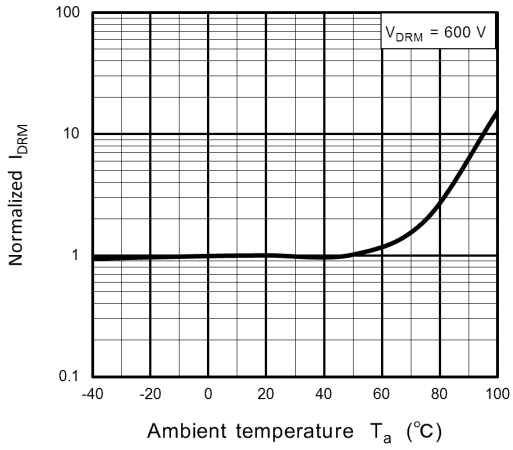


Fig. 12.8 Normalized I_{DRM} - T_a

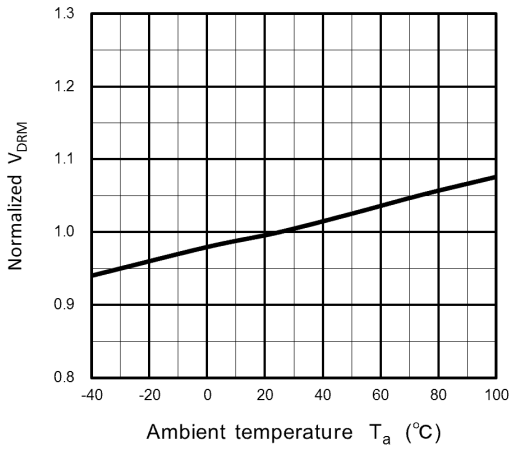


Fig. 12.9 Normalized V_{DRM} - T_a

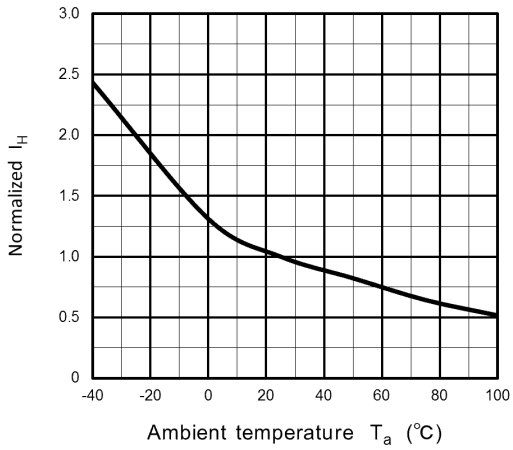


Fig. 12.10 Normalized I_H - T_a

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

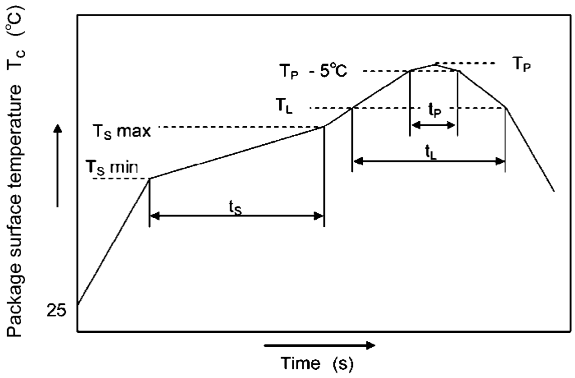
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13. Soldering and Storage

13.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

- When using soldering reflow.
  The soldering temperature profile is based on the package surface temperature.
  (See the figure shown below, which is based on the package surface temperature.)
  Reflow soldering must be performed once or twice.
  The mounting should be completed with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	T_S	150	200	°C
Preheat time	t_S	60	120	s
Ramp-up rate (T_L to T_P)			3	°C/s
Liquidus temperature	T_L	217		°C
Time above T_L	t_L	60	150	s
Peak temperature	T_P		260	°C
Time during which T_c is between (T_P – 5) and T_P	t_P		30	s
Ramp-down rate (T_P to T_L)			6	°C/s

Fig. 13.1.1 An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

- When using soldering flow
  Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds.
  Mounting condition of 260 °C within 10 seconds is recommended.
  Flow soldering must be performed once.
- When using soldering Iron
  Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C
  Heating by soldering iron must be done only once per lead.

13.2. Precautions for General Storage

- Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45% to 75%, respectively.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.

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14. Land Pattern Dimensions (for reference only)

(Unit: mm)

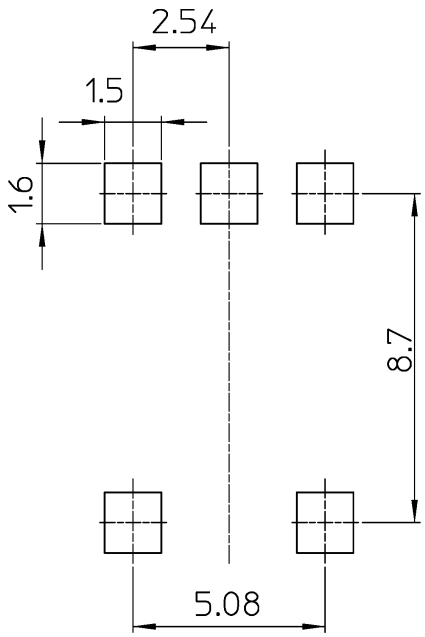


Fig. 14.1 TLP3052A
Lead forming and taping option
(LF1), (TP1), (LF5), (TP5)

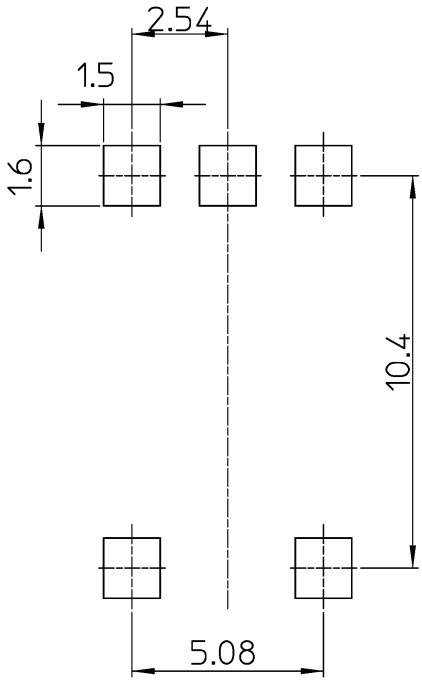


Fig. 14.2 TLP3052AF
Lead forming and taping option
(LF4), (TP4)

15. EN IEC 60747-5-5 Option (D4) Specification

- Part number: TLP3052A **(Note 1)**
- The following part naming conventions are used for the devices that have been qualified according to option (D4) of EN IEC 60747.

  Example: TLP3052A(D4TP1,F

  D4: EN IEC 60747 option
  TP1: Tape type
  F: [[G]]/RoHS COMPATIBLE **(Note 2)**

Note 1: Use TOSHIBA standard type number for safety standard application.
e.g., TLP3052A(D4TP1,F → TLP3052A

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.
RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Description		Symbol	Rating	Unit
Application classification for rated mains voltage ≤ 300 Vrms for rated mains voltage ≤ 600 Vrms			 I-IV I-III	—
Climatic classification			40 / 100 / 21	—
Pollution degree			2	—
Maximum operating insulation voltage	TLPxxxx type	V_{IORM}	890	Vpeak
	TLPxxxxF type		1140	
Input to output test voltage, Method A V_{pr} = 1.6 × V_{IORM}, type and sample test t_p = 10 s, partial discharge < 5 pC	TLPxxxx type	V_{pr}	1424	Vpeak
	TLPxxxxF type		1824	
Input to output test voltage, Method B V_{pr} = 1.875 × V_{IORM}, 100 % production test t_p = 1 s, partial discharge < 5 pC	TLPxxxx type	V_{pr}	1670	Vpeak
	TLPxxxxF type		2140	
Highest permissible overvoltage (transient overvoltage, t_{pr} = 60 s)		V_{TR}	8000	Vpeak
Safety limiting values (max. permissible ratings in case of fault, also refer to thermal derating curve) current (input current I_F, P_{so} = 0) power (output or total power dissipation) temperature		 I_{si} P_{so} T_s	 400 700 150	 mA mW °C
Insulation resistance	V_{IO} = 500 V, T_a = 25 °C V_{IO} = 500 V, T_a = 100 °C V_{IO} = 500 V, T_a = T_s	R_{si}	≥ 10^{12} ≥ 10^{11} ≥ 10^{9}	Ω

Fig. 15.1 EN IEC 60747 Insulation Characteristics

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Table 15.1 Insulation Related Specifications (Note)

Insulation Related Parameters	Symbol	TLP3052A	TLP3052AF
Minimum creepage distance	Cr	7.0 mm	8.0 mm
Minimum clearance	Cl	7.0 mm	8.0 mm
Minimum insulation thickness	ti	0.4 mm	0.4 mm
Comparative tracking index	CTI	500	500

Note: If a printed circuit is incorporated, the creepage distance and clearance may be reduced below this value. (e. g., at a standard distance between soldering eye centers of 7.5 mm). If this is not permissible, the user shall take suitable measures.

Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.



Fig. 15.2 Marking on packing

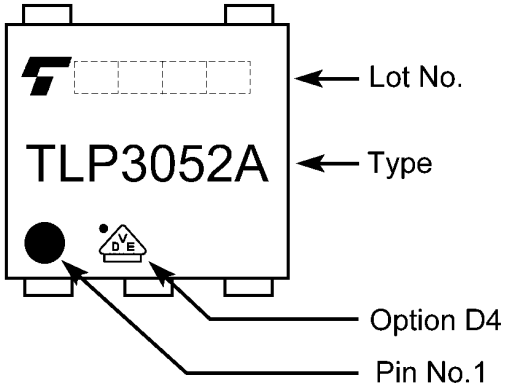


Fig. 15.3 Marking Example (Note)

Note: The above marking is applied to the photocouplers that have been qualified according to option (D4) of EN IEC 60747.

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Figure 1 Partial discharge measurement procedure according to EN IEC 60747
Destructive test for qualification and sampling tests.

Method A

(for type and sampling tests, destructive tests)

t_1, t_2	= 1 to 10 s
t_3, t_4	= 1 s
t_p (Measuring time for partial discharge)	= 10 s
t_b	= 12 s
t_{ini}	= 60 s

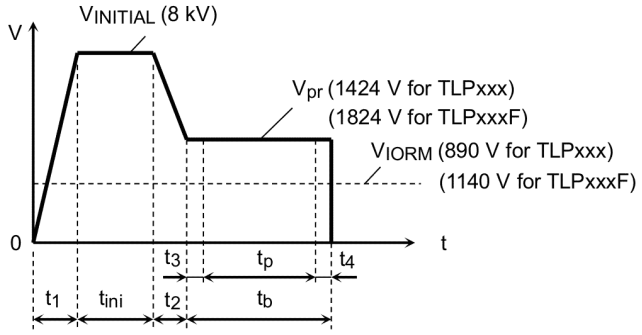


Figure 2 Partial discharge measurement procedure according to EN IEC 60747
Non-destructive test for 100 % inspection.

Method B

(for sample test, non-destructive test)

t_3, t_4	= 0.1 s
t_p (Measuring time for partial discharge)	= 1 s
t_b	= 1.2 s

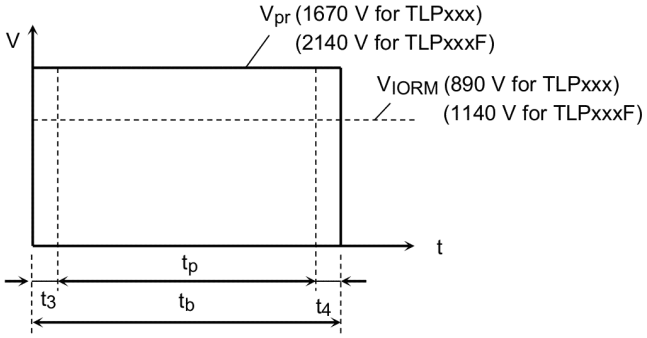


Figure 3 Dependency of maximum safety ratings on ambient temperature

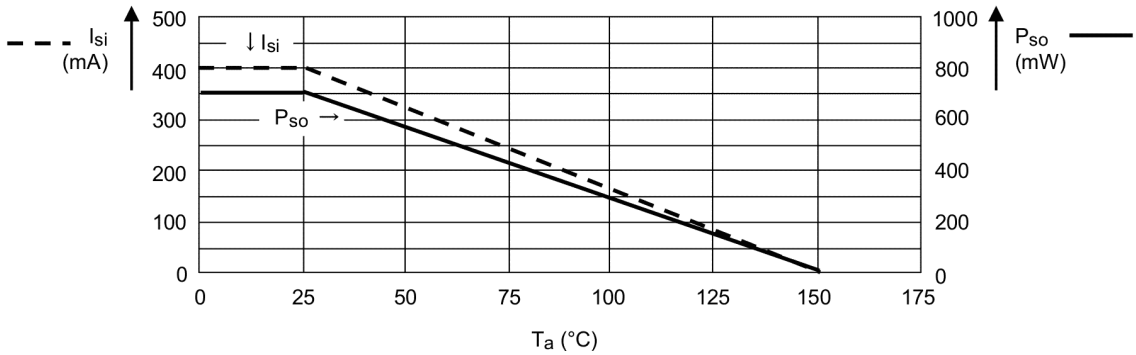


Fig. 15.4 Measurement Procedure

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16. Ordering Information (Example of Item Name)

Item Name	Packaging (Note 1)	VDE Option	Packing (MOQ)
TLP3052A(F	TH		Magazine (50 pcs)
TLP3052A(LF1,F	LF1		Magazine (50 pcs)
TLP3052A(LF5,F	LF5		Magazine (50 pcs)
TLP3052A(TP1,F	LF1		Tape and reel (1500 pcs)
TLP3052A(TP5,F	LF5		Tape and reel (1500 pcs)
TLP3052A(D4,F	TH	EN IEC 60747-5-5	Magazine (50 pcs)
TLP3052A(D4LF1,F	LF1	EN IEC 60747-5-5	Magazine (50 pcs)
TLP3052A(D4LF5,F	LF5	EN IEC 60747-5-5	Magazine (50 pcs)
TLP3052A(D4TP1,F	LF1	EN IEC 60747-5-5	Tape and reel (1500 pcs)
TLP3052A(D4TP5,F	LF5	EN IEC 60747-5-5	Tape and reel (1500 pcs)
TLP3052AF(F	TH, Wide forming		Magazine (50 pcs)
TLP3052AF(LF4,F	LF4, Wide forming		Magazine (50 pcs)
TLP3052AF(TP4,F	LF4, Wide forming		Tape and reel (1000 pcs)
TLP3052AF(D4,F	TH, Wide forming	EN IEC 60747-5-5	Magazine (50 pcs)
TLP3052AF(D4LF4F	LF4, Wide forming	EN IEC 60747-5-5	Magazine (50 pcs)
TLP3052AF(D4TP4F	LF4, Wide forming	EN IEC 60747-5-5	Tape and reel (1000 pcs)

Note 1: TH: Through-hole, LF: Lead forming for surface mount

17. Devices in Halogen-Free Resin Packages

・This product is Halogen-Free

Toshiba Electronic Devices & Storage Corporation ("Toshiba") defines a "Halogen-Free resin semiconductor product" as a semiconductor product in which:

(1) the encapsulating resins do not contain any of the following elements: bromine (Br), chlorine (Cl) and antimony (Sb), respectively, in an amount exceeding 0.09 weight percent, and do not contain chlorine and bromine in an aggregate amount exceeding 0.15 weight percent of the encapsulating resins, and/or

(2) the resin portion(s) in printed circuit boards do not contain any of the following elements: bromine, chlorine and antimony, respectively, in an amount exceeding 0.09 weight percent, and do not contain chlorine and bromine in an aggregate amount exceeding 0.15 weight percent of the each resin portion(s) in printed circuit boards.

For avoidance of doubt, "Halogen-Free resin semiconductor product" does not mean, and Toshiba does not make any warranty of any kind, that said semiconductor product is entirely free of antimony or of any of the following elements of the halogen family: bromine, chlorine, iodine (I), fluorine (F) and astatine (At).

In addition, a Halogen-Free resin semiconductor product may contain antimony and/or any of the elements of the halogen family as mentioned in the above paragraph in one or more portion(s) of the semiconductor product other than the encapsulating resins and the resin portion(s) in printed circuit boards.

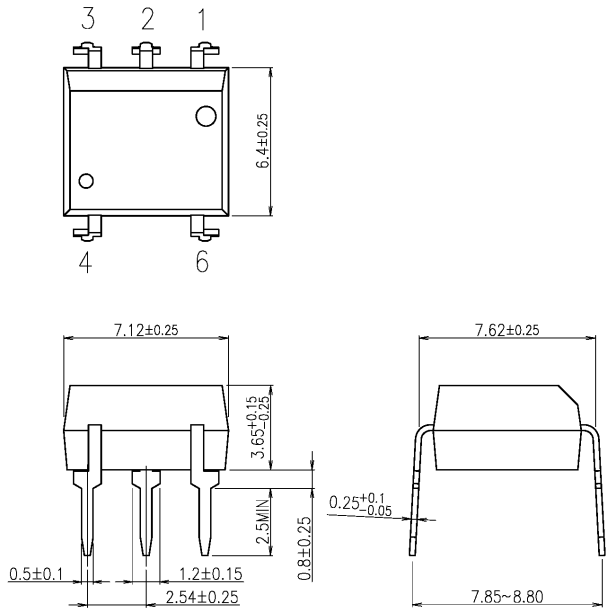
The information provided herein is accurate as of the date that it was provided, to the best of the knowledge and belief of the Toshiba Electronic Devices & Storage Corporation ("Toshiba"), Toshiba bases such knowledge and belief on information provided by third parties, and Toshiba makes no representation or warranty as to the accuracy of such third party information. Toshiba has taken and will continue to take, reasonable steps to provide accurate information to its customers, but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals.

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Package Dimensions

Unit: mm

TLP3052A



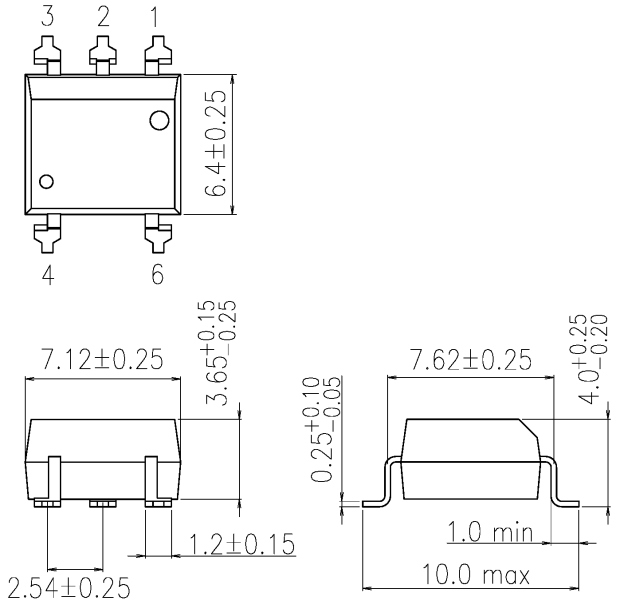
Weight: 0.40 g (typ.)

Package Name(s)
TOSHIBA: 11-7A10S

Package Dimensions

Unit: mm

TLP3052A(LF1,TP1)



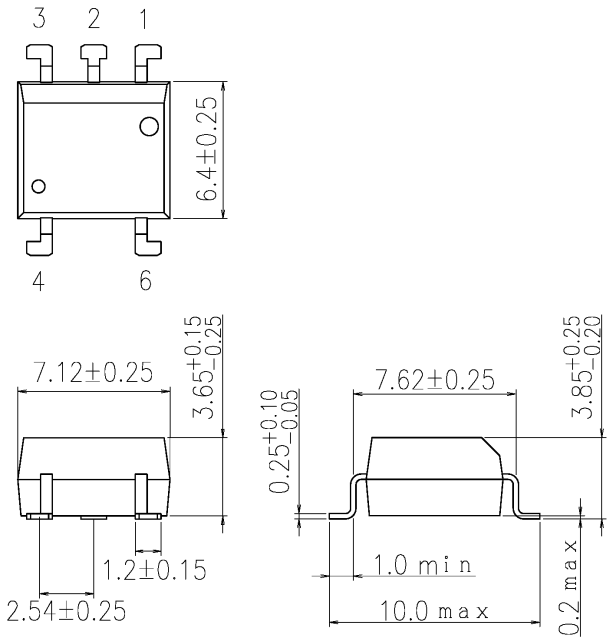
Weight: 0.39 g (typ.)

Package Name(s)
TOSHIBA: 11-7A1001S

Package Dimensions

Unit: mm

TLP3052A(LF5,TP5)



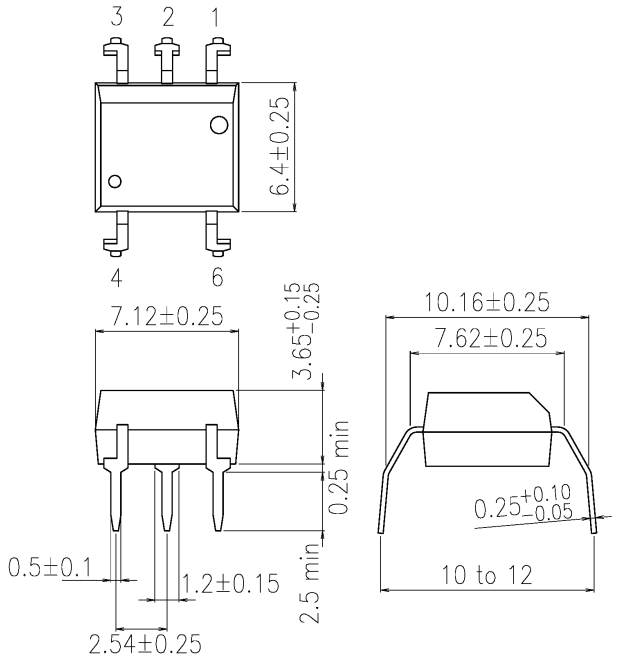
Weight: 0.39 g (typ.)

Package Name(s)
TOSHIBA: 11-7A1005S

Package Dimensions

Unit: mm

TLP3052AF



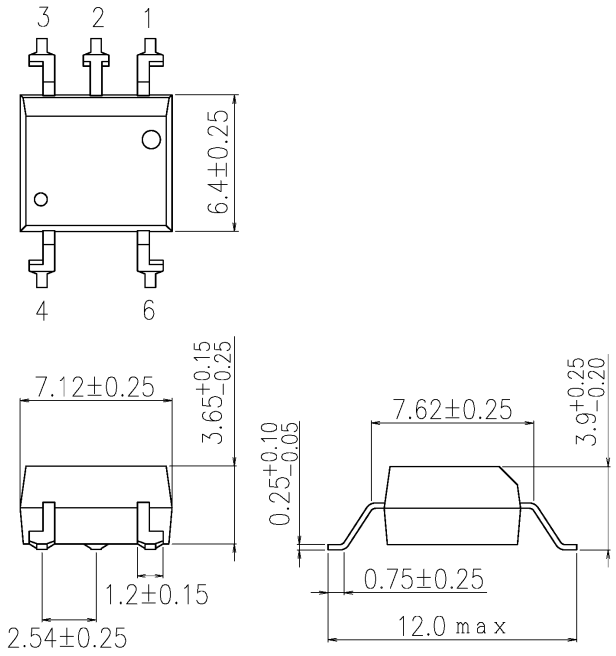
Weight: 0.40 g (typ.)

Package Name(s)
TOSHIBA: 11-7A1002S

Package Dimensions

Unit: mm

TLP3052AF(LF4,TP4)



Weight: 0.39 g (typ.)

Package Name(s)
TOSHIBA: 11-7A1004S

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